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View Online at https://aerobasegroup.com/nsn/5961-01-103-4880 **Inclosure Material:** Glass **Overall Length:** 0.357 inches **Terminal Length:** 1.000 inches **Overall Diameter:** 0.235 inches Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Electrode Internally-electrically Connected To Case:** Cathode **Mounting Method: Terminal Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 53.6 breakdown voltage, dc **Current Rating Per Characteristic:** 1.00 amperes forward current, average peak **Power Rating Per Characteristic:** 1.0 watts small-signal input power, common-collector major **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Precious Material And Location:** Terminals gold **Precious Material:** Gold **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 uninsulated wire lead **Specification Data:** 81349-mil-s-19500/500 government specification Shelf Life: N/a **Unit Of Measure:**

No

Demilitarization:

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